EAST - [10707826.wsp 1]

File View Edit Tools Window Help

Drafts
Pending
Active
L1: (101086) (flash near memory or non-volatile near memory)
L2: (22822) floating near gate$1
L3: (11968) 1 and 2
L4: (163) 3 and concave
L5: (2586) 3 and stack$2 near gate
L6: (2379) 5 and (oxide dielectric)
L8: (1) 7 and concave
L7: (63) 6 and (erase near gate) and (select near gate)
L9: (19146) 1 and (NAND NOR)
L10: (16) 9 and (floating near gate with concave)
L11: (49) 1 and (floating near gate with concave) and control near gate
L12: (6927) 1 and (floating near gate) and control near gate
L13: (39) 1 and (floating near gate) and control near gate and erase near gate and select near ga...
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Default operator: OR | Stems | Highlight search terms

1 and (floating near gate with concave) and control near gate

Structure | Image | Text | HTML

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
33			US 6482700 B2	20021119	10	Split gate field effect transistor (FET) device with enhanced electrode registration and method for fabrication thereof	438/267	257/E21.682; 257/E27.103; 257/E29.129
34			US 6469341 B1	20021022	14	Method and device for producing undercut gate for flash memory	257/316	257/E21.209; 257/E27.103; 257/E29.129
35			US 6468863 B2	20021022	9	Split gate field effect transistor (FET) device employing dielectric barrier layer and method for fabrication thereof	438/261	257/E21.682; 257/E27.103; 257/E29.129
36			US 6387757 B1	20020514	8	Sacrificial self aligned spacer layer ion implant mask method for forming a split gate field effect transistor (FET) device	438/266	257/E21.682; 257/E27.103
37			US 6372617 B1	20020416	12	Method of manufacturing non-volatile memory	438/593	257/E21.209; 257/E21.422; 438/594
38			US 6355525 B1	20020312	16	Method of producing non-volatile semiconductor memory device having a floating gate with protruding conductive side-wall portions	438/257	257/E21.209; 257/E21.422; 257/E29.129
39			US 6317360 B1	20011113	54	Flash memory and methods of writing and erasing the same as well as a method of forming the same	365/185.01	257/315; 257/E21.209; 257/E21.422
40			US 6248631 B1	20010619	15	Method for forming a v-shaped floating gate	438/260	257/E21.682; 257/E27.103; 438/254
41			US 6245613 B1	20010612	12	Field effect transistor having a floating gate	438/259	257/E21.209; 257/E21.688; 438/257
42			US 6204122 B1	20010320	18	Methods of forming nonvolatile integrated circuit memory devices having high capacitive coupling ratios	438/257	257/E21.209; 257/E21.682; 257/E29.129
43			US 6172394 B1	20010109	16	Non-volatile semiconductor memory device having a floating gate with protruding conductive side-wall portions	257/315	257/268; 257/387; 257/E21.209

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